Alfa-MOS Technology

AFN1501S
100V N-Channel Enhancement Mode MOSFET

General Description

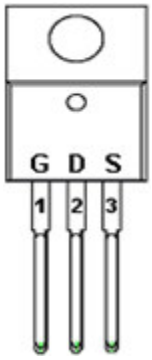
AFN1501S, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

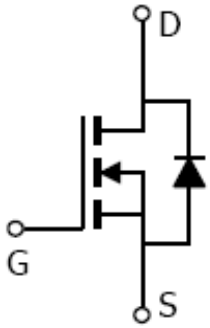
These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

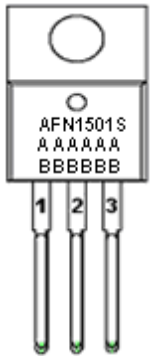
Features

- 100V/60A, $R_{DS(ON)}$= 6.4mΩ@V_{GS}=10V
- Super high density cell design for extremely low $R_{DS\ (ON)}$
- TO-220-3L package design

Pin Description (TO-220-3L)







Application

- Power Supply - Secondary Synchronous Rectification
- Industrial
- Primary Switch

Pin Define

Pin	Symbol	Description
1	G	Gate
2	D	Drain
3	S	Source

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN1501ST220TG	AFN1501S AAAAAA BBBBBB	TO-220-3L	Tube	50 EA

※ A Lot code
※ B Date code
※ AFN1501ST220TG : Tube ; Pb- Free ; Halogen- Free

Absolute Maximum Ratings

(T_A=25℃ Unless otherwise noted)

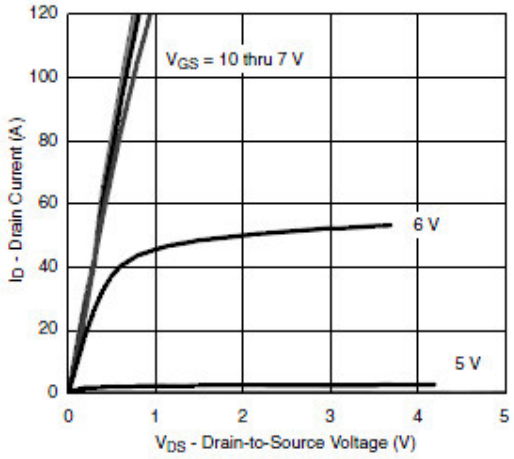
Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	100	V
Gate –Source Voltage		V_{GSS}	±20	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	120	A
	T_A=70℃		90	
Pulsed Drain Current		I_{DM}	350	
Continuous Source Current(Diode Conduction)		I_S	100	
Single Pulse Avalanche Current		I_{AS}	60	
Power Dissipation	T_A=25℃	P_D	75	W
Operating Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	62.5	℃/W

Electrical Characteristics

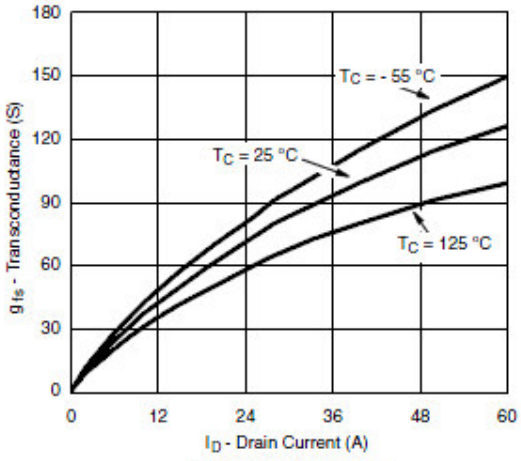
(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	100			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	2.0		4.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=80V,V_{GS}=0V			1	uA
		V_{DS}=80V,V_{GS}=0V T_J=85℃			30	
On-State Drain Current	$I_{D(on)}$	V_{DS}≧10V,V_{GS}=10V	70			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=60A		5.6	6.4	mΩ
Forward Transconductance	g_{FS}	V_{DS}=15V,I_D=20A		62		S
Diode Forward Voltage	V_{SD}	I_S=30A,V_{GS}=0V		0.8	1.3	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=50V,V_{GS}=10V I_D≡85A		95	115	nC
Gate-Source Charge	Q_{gs}			45		
Gate-Drain Charge	Q_{gd}			35		
Input Capacitance	C_{iss}	V_{DS}=50V,V_{GS}=0V f=1MHz		6250		pF
Output Capacitance	C_{oss}			580		
Reverse Transfer Capacitance	C_{rss}			235		
Turn-On Time	$t_{d(on)}$	V_{DD}=50V,R_L=0.6Ω I_D≡85A,V_{GEN}=10V R_G=1Ω		32	65	ns
	t_r			25	55	
Turn-Off Time	$t_{d(off)}$			40	80	
	t_f			15	40	

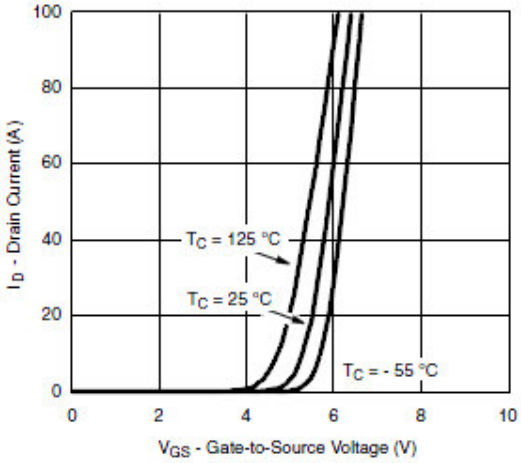
Typical Characteristics



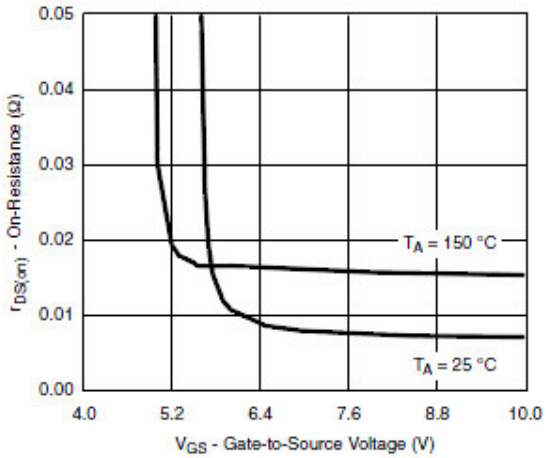
Output Characteristics



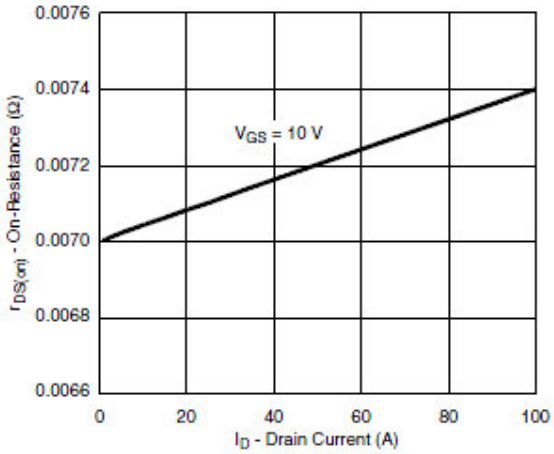
Transconductance



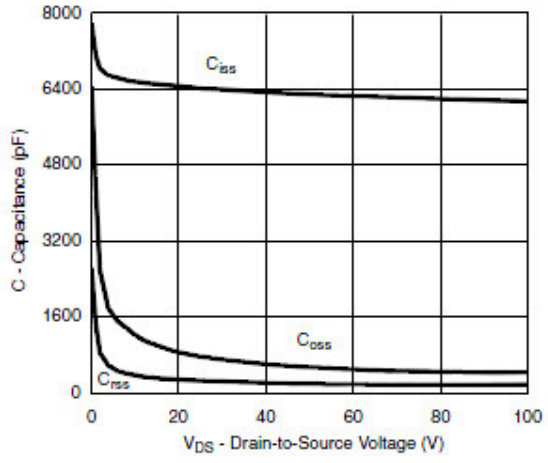
Transfer Characteristics



On-resistance vs. Gate-to-Source Voltage

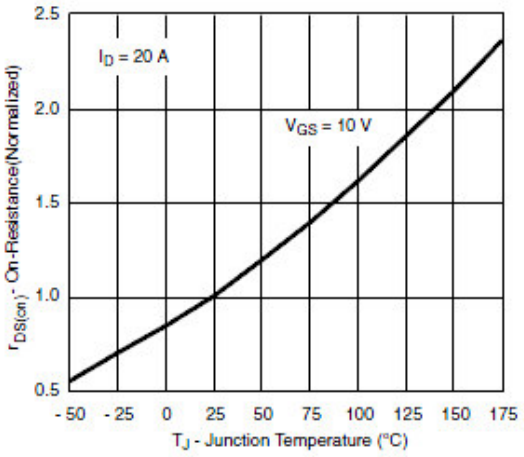


On-Resistance vs. Drain Current

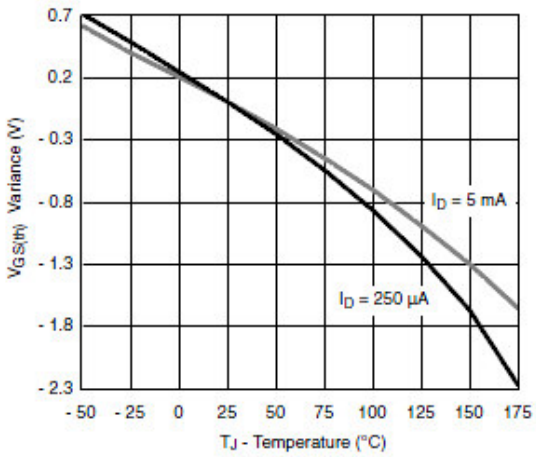


Capacitance

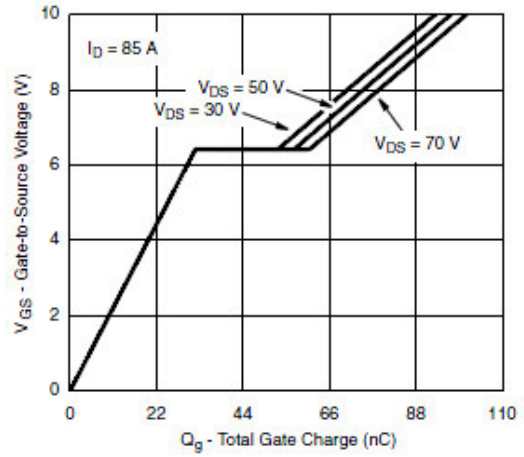
Typical Characteristics



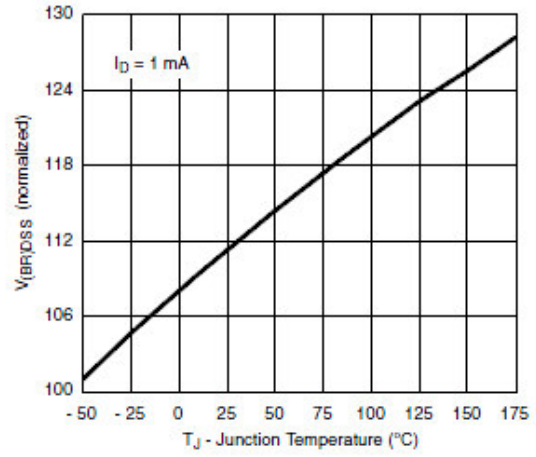
On-Resistance vs. Junction Temperature



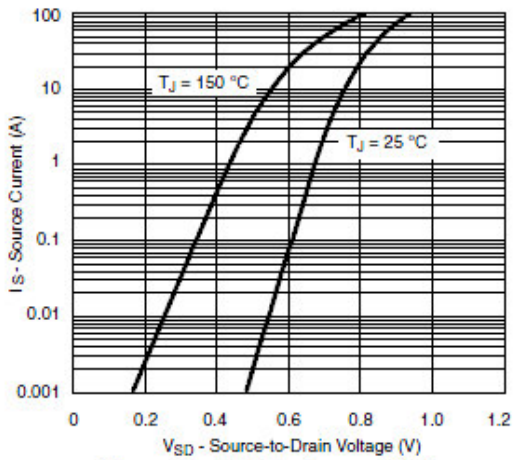
Threshold Voltage



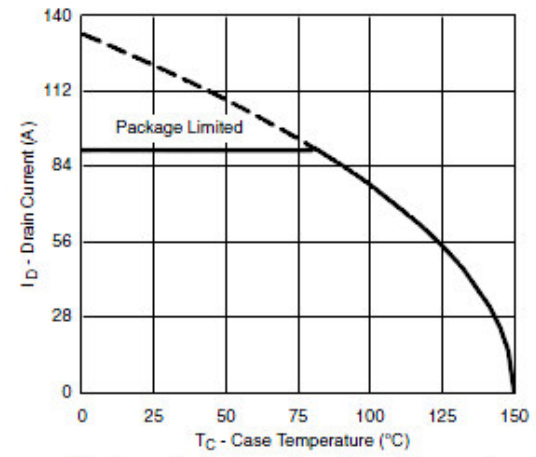
Gate Charge



Drain Source Breakdown vs. Junction Temperature

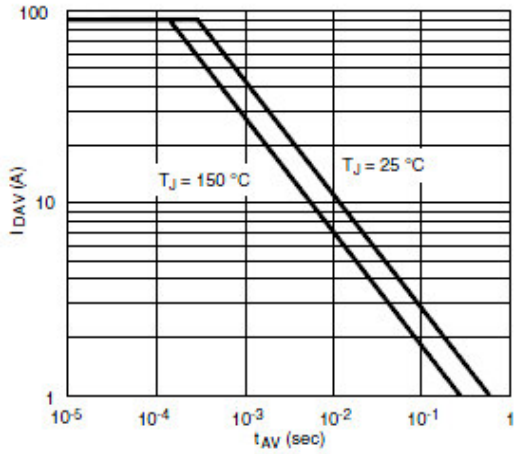


Source-Drain Diode Forward Voltage

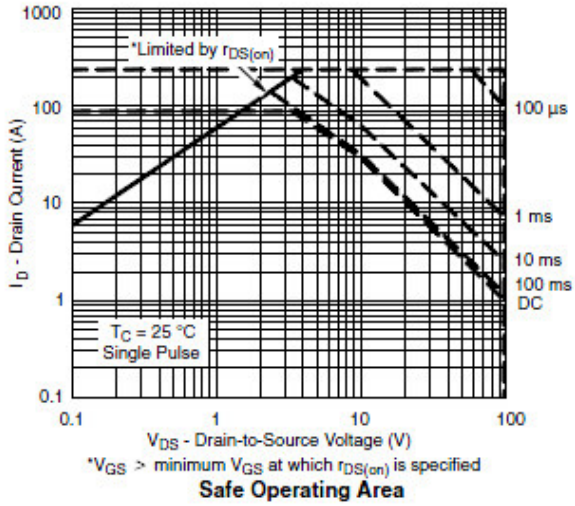


Maximum Drain Current vs. Case Temperature

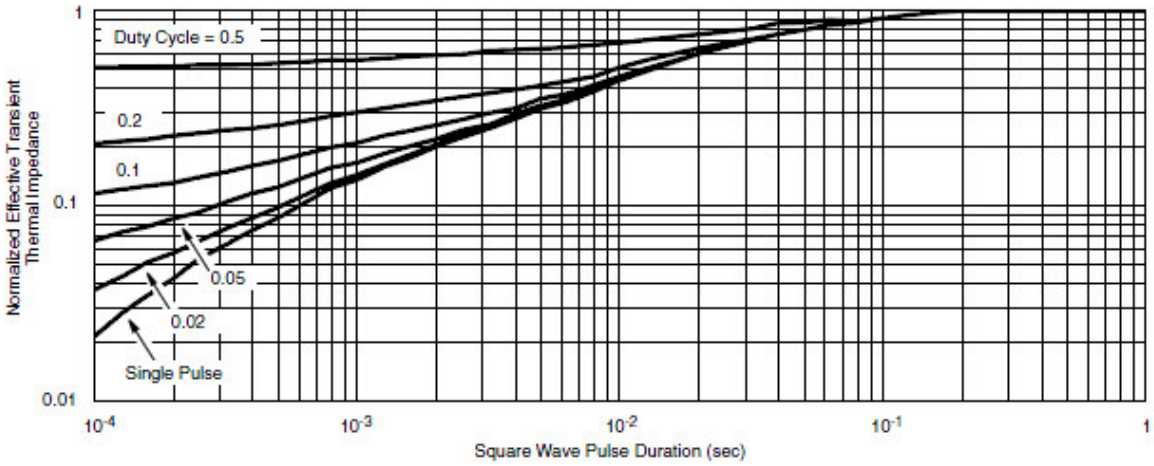
Typical Characteristics



Single Pulse Avalanche Current Capability vs. Time



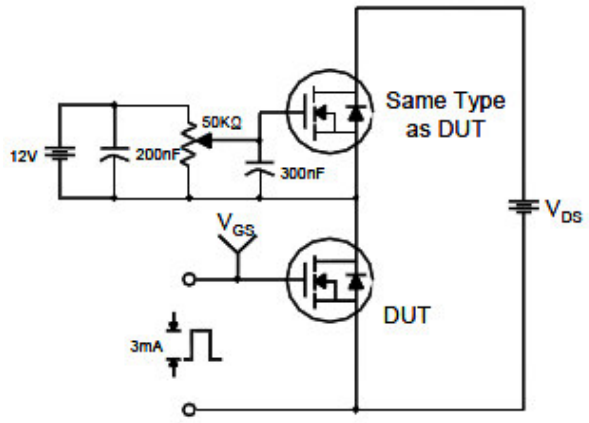
Safe Operating Area

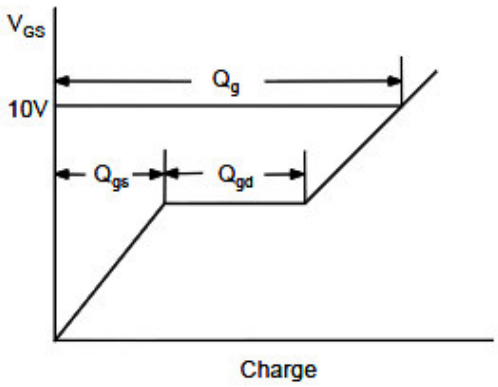


Normalized Thermal Transient Impedance, Junction-to-Case

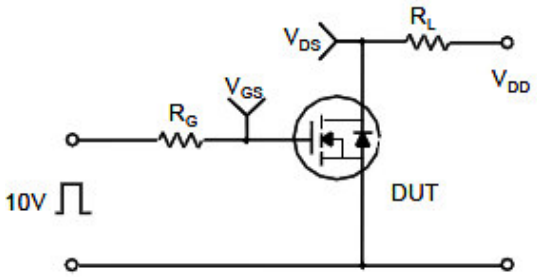
Typical Characteristics

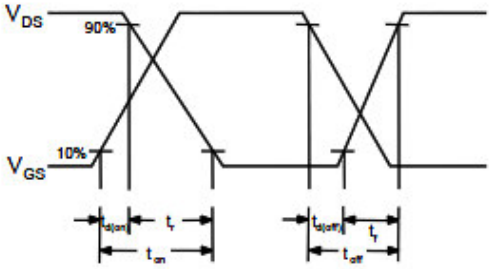
Gate Charge Test Circuit & Waveform



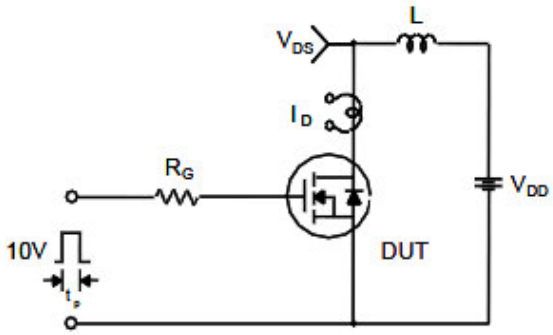


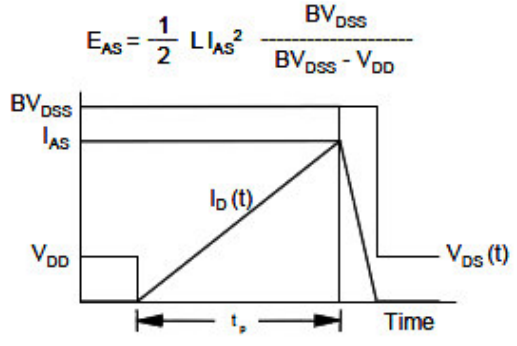
Resistive Switching Test Circuit & Waveforms



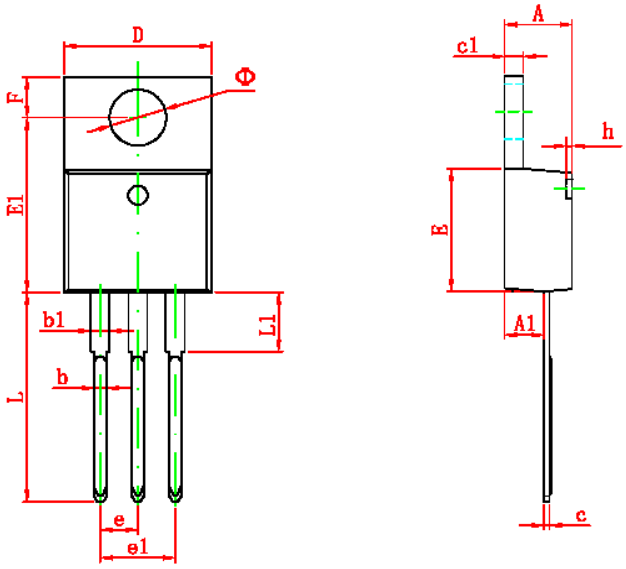


Unclamped Inductive Switching Test Circuit & Waveforms





Package Information (TO-220-3L)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.470	4.670	0.176	0.184
A1	2.520	2.820	0.099	0.111
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
E1	12.060	12.460	0.475	0.491
e	2.540 TYP		0.100 TYP	
e1	4.980	5.180	0.196	0.204
F	2.590	2.890	0.102	0.114
h	0.000	0.300	0.000	0.012
L	13.400	13.800	0.528	0.543
L1	3.560	3.960	0.140	0.156
• •	3.735	3.935	0.147	0.155

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